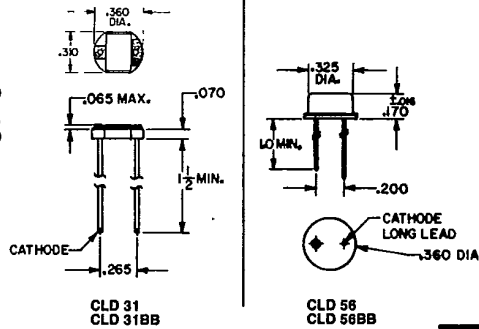


T-41-51

## Product Data

CLD31  
CLD56  
CLD31BB  
CLD56BB

Silicon Planar  
Photovoltaic Diodes

The anode of "V" versions are identified by a color dot

4

**GENERAL DESCRIPTION** — The CLD Series of Photodiodes is specifically designed to optimize Photovoltaic characteristics. They are all Silicon PN Planar diodes, with 2 diodes in hermetic bases for stringent environmental applications and 2 epoxy encapsulated devices for lower cost applications. All diodes offer high linearity, low dark current, and fast response for use in critical measurement applications. These units are also available with a special filter material to block out response to visible light; CLD31V.

**ABSOLUTE MAXIMUM RATINGS****Maximum Temperatures**

Storage Temperature  $-35^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$   
Operating Junction Temperature  $+150^{\circ}\text{C}$   
Storage, Operating Temperature of Epoxy  
Encapsulated Device  $-30^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  (5)

All dimensions  $\pm .005$  except as noted.

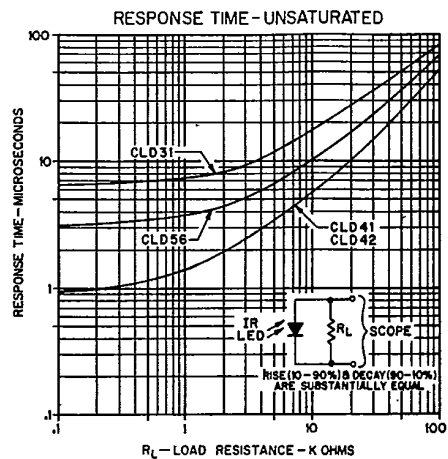
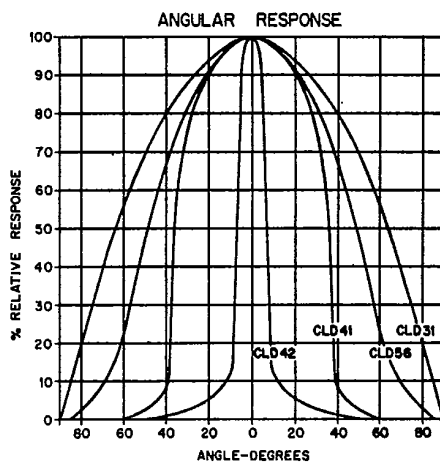
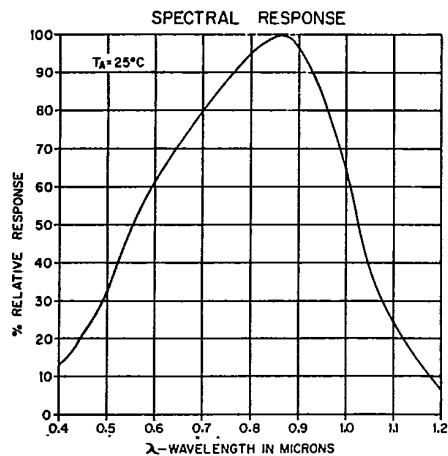
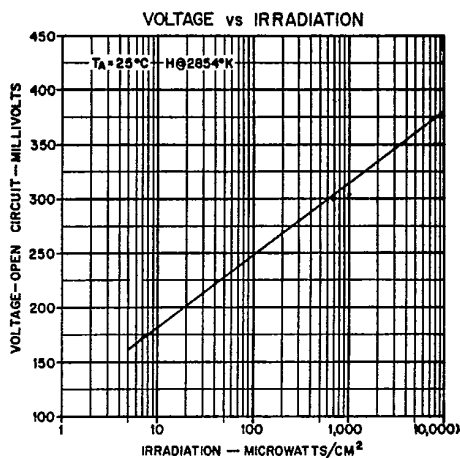
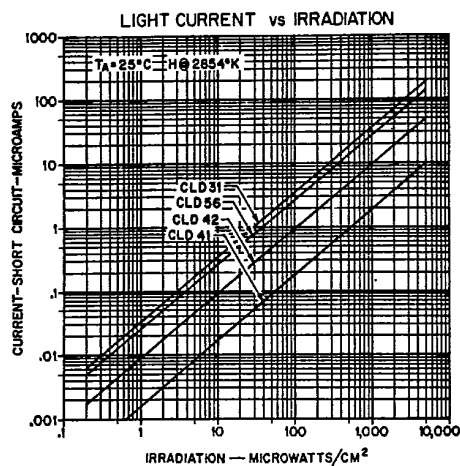
**ELECTRICAL CHARACTERISTICS (25°C Free Air unless otherwise designated.)**

| Symbol                          | Characteristics                                      | CLD31        |      | CLD31BB     |      | CLD56       |      | CLD56BB     |      | Unit   |
|---------------------------------|------------------------------------------------------|--------------|------|-------------|------|-------------|------|-------------|------|--------|
|                                 |                                                      | Min.         | Max. | Min.        | Max. | Min.        | Max. | Min.        | Max. |        |
| LXW                             | Active Area                                          | .222 x .122  |      | .222 x .122 |      | .222 x .122 |      | .222 x .122 |      | inches |
| I <sub>sc</sub>                 | Short Circuit Current (1)<br>H = 5mw/cm <sup>2</sup> | 150          |      | 150         |      | 100         |      | 100         |      | μA     |
| V <sub>oc</sub>                 | Open Circuit Voltage (1)<br>H = 5mw/cm <sup>2</sup>  | .35 Typ.     |      | .35 Typ.    |      | .35 Typ.    |      | .35 Typ.    |      | Volts  |
| I <sub>D</sub>                  | Dark Current V = 100 mv<br>H = 0 V = -15 v           |              | 100  |             | 50   |             | 100  |             | 50   | nA     |
| C <sub>J</sub>                  | Junction Capacitance (2)                             |              | 400  |             | 400  |             | 400  |             | 400  | pf     |
| t <sub>r</sub> , t <sub>f</sub> | Rise or Fall time (3)                                |              | 10   |             | 10   |             | 10   |             | 10   | μsec   |
| ΔT <sub>sc</sub>                | Temperature Coefficient I <sub>sc</sub><br>(1) (4)   | +.2% Typical |      |             |      |             |      |             |      | %/C°   |
|                                 | Peak Spectral Response                               | 8600 Typ.    |      | 8600 Typ.   |      | 8600 Typ.   |      | 8600 Typ.   |      | Å      |

- (1) Light source is a frosted tungsten incandescent lamp at 2854°K.
- (2) Measured at 0 bias with f = 1MHZ.
- (3) Measured in an unsaturated condition with an IR source and a load resistor of 1Kohms.
- (4) Typical open circuit voltage temperature coefficient is -2mV/°C.
- (5) Can supply units rated for 100 C

Consult factory for special I<sub>D</sub> selections

T-41-51



PHOTOVOLTAIC DIODE EQUIVALENT CIRCUIT

